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SD101A THRU SD101C

Small Signal Schottky Diodes

Features

- Low Reverse Recovery Time
- Low Reverse Capacitance
- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection

Mechanical Data

- Case: DO-35, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Indicated by Cathode Band

Maximum Ratings @ 25°C Unless Otherwise Specified

Characteristic	Symbol	SD101A	SD101B	SD101C
Peak Repetitive Reverse Voltage	V_{RRM}			
Working Peak Reverse Voltage	V_{RWM}	60V	50V	40V
DC Blocking Voltage	V_R			
RMS Reverse Voltage	$V_{R(RMS)}$	42V	35V	28V
Maximum single cycle surge 10us square wave	I_{FSM}	2.0A		
Power Dissipation(Note 1)	P_d	400mW		
Thermal Resistance, Junction to Ambient	R	300K/W		
Junction Temperature	T_j	125°C		
Operation/Storage Temp. Range	T_{STG}	-55 to +150°C		

Electrical Characteristics @ 25°C Unless Otherwise Specified

Characteristic	Symbol	Max	Test Condition
Leakage Current	SD101A SD101B SD101C	200nA 200nA 200nA	$V_R=50V$ $V_R=40V$ $V_R=30V$
Maximum Forward Voltage Drop	SD101A SD101B SD101C	0.41V 0.4V 0.39V	$I_F=1mA$ $I_F=15mA$
Junction Cap.	SD101A SD101B SD101C	2.0pF 2.1pF 2.2pF	$V_R=0V, f=1.0MHz$
Reverse Recovery Time	t_{rr}	1ns	$I_F=I_R=50mA, \text{recover to } 200mA/0.1I_R$

DO-35

DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	---	.166	---	4.2	
B	---	.079	---	2.00	
C	---	.020	---	.52	
D	1.000	---	25.40	---	

Note: 1. Valid provided that electrodes are kept at ambient temperature

SD101A thru SD101C



Figure 1. Typical variation of forward current vs. fwd. Voltage for primary conduction through the schottky barrier

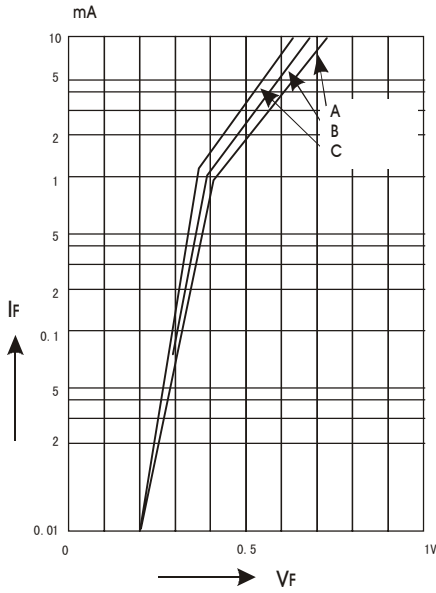


Figure 2. Typical forward conduction curve of combination Schottky barrier and PN junction guard ring

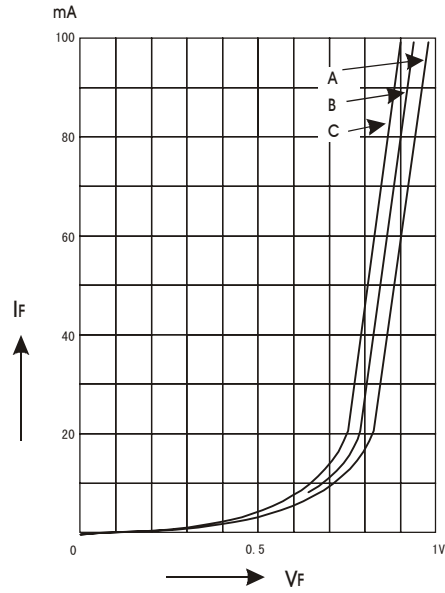


Figure 3. Typical variation of reverse current at versus temperature

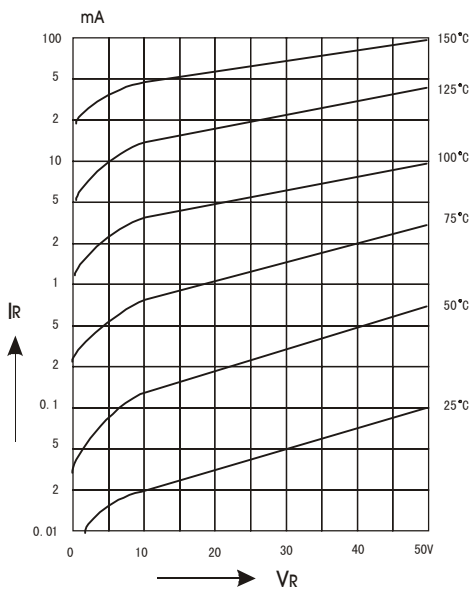


Figure 4. Typical capacitance curve as a function of reverse voltage

